

## 1. General description

Silicon Carbide Schottky diode in a TO247-2L plastic package, designed for high frequency switched-mode power supplies.



## 2. Features and benefits

- Highly stable switching performance
- High forward surge capability  $I_{FSM}$
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability ( $T_{j(max)} = 175\text{ °C}$ )

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

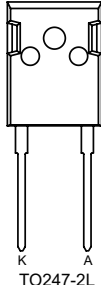

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{RRM}$	repetitive peak reverse voltage			1200			V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 114\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		30			A
$T_j$	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_F$	forward voltage	$I_F = 30\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 5</a>	-	1.42	1.60	V	
		$I_F = 30\text{ A}$ ; $T_j = 150\text{ °C}$ ; <a href="#">Fig. 5</a>	-	1.90	2.30	V	
		$I_F = 30\text{ A}$ ; $T_j = 175\text{ °C}$ ; <a href="#">Fig. 5</a>	-	2.00	2.50	V	
<b>Dynamic characteristics</b>							
$Q_r$	recovered charge	$I_F = 30\text{ A}$ ; $di_F/dt = 500\text{ A}/\mu\text{s}$ ; $V_R = 400\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	68	-	nC	

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
mb	mb	mounting base; connected to cathode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2D301200W	TO247-2L	WNSC2D301200W6Q	Tube	30	TO247L-2L	10-Nov-2020

## 7. Marking

Table 4. Marking codes

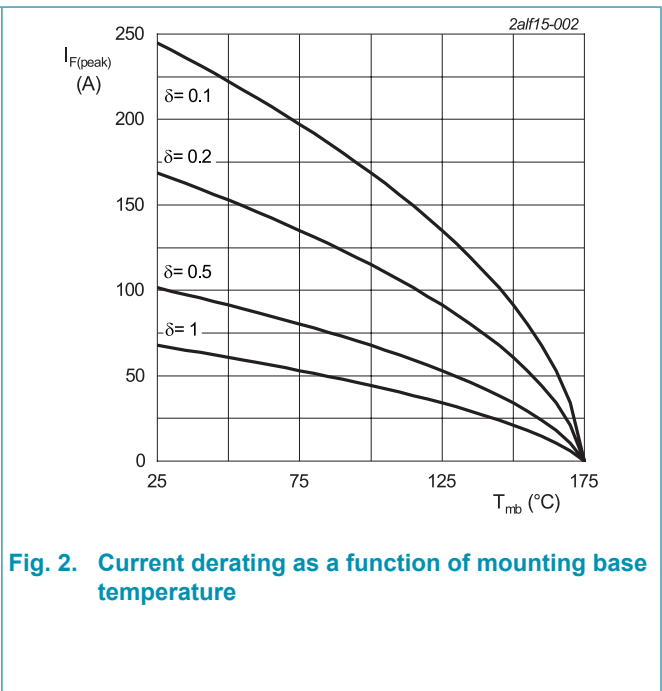
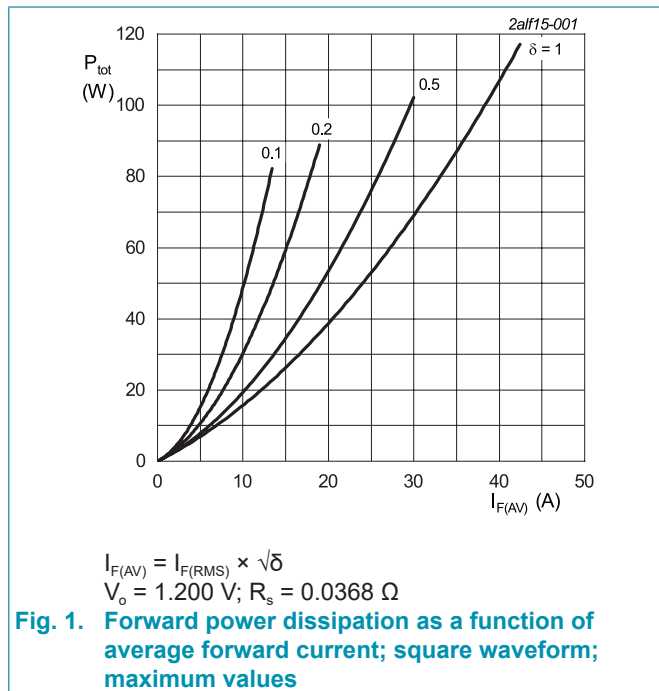
Type number	Marking codes
WNSC2D301200W	WNSC2D 301200W

### 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			1200	V
$V_{RWM}$	crest working reverse voltage			1200	V
$V_R$	reverse voltage	DC		1200	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} 114 \leq \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		30	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25 \mu\text{s}$ ; $T_{mb} \leq 114 \text{ }^\circ\text{C}$ ; square-wave pulse		60	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10 \text{ ms}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; sine-wave pulse		270	A
		$t_p = 10 \mu\text{s}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; square-wave pulse		1500	A
$I^2t$	$I^2t$ for fusing	sine-wave pulse; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $t_p = 10 \text{ ms}$		364.5	$\text{A}^2\text{s}$
$T_{stg}$	storage temperature			-55 to 175	$^\circ\text{C}$
$T_j$	junction temperature			-55 to 175	$^\circ\text{C}$



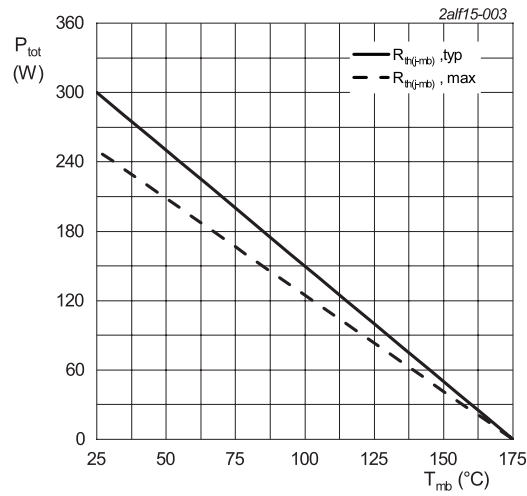


Fig. 3. Total power dissipation as a function of mounting base temperature

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 4</a>		-	0.5	0.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

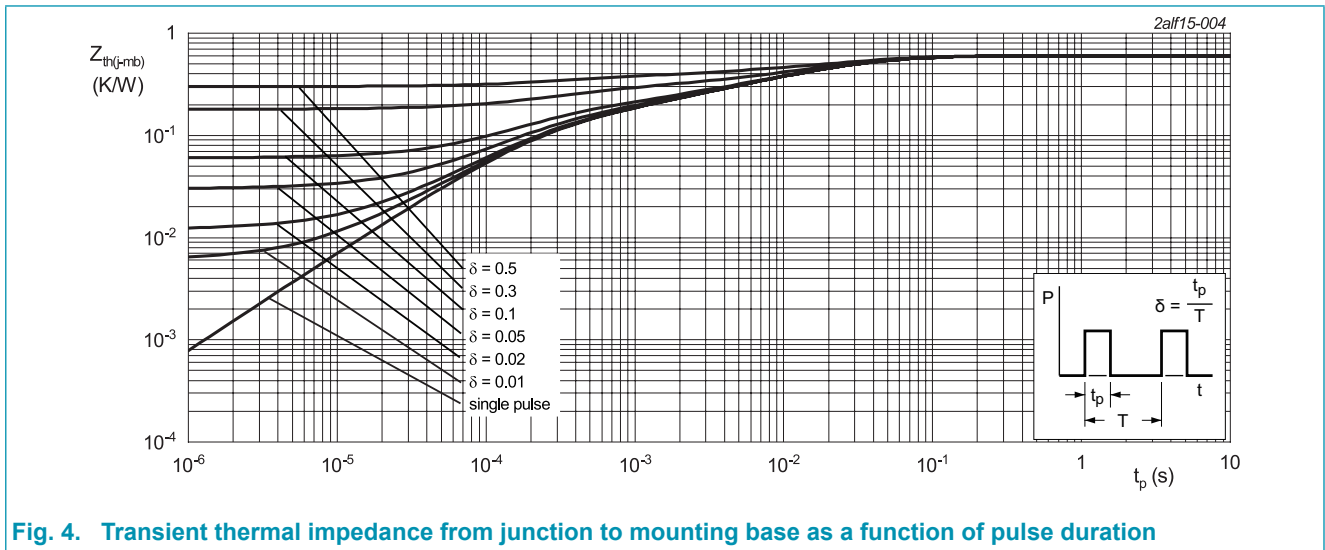
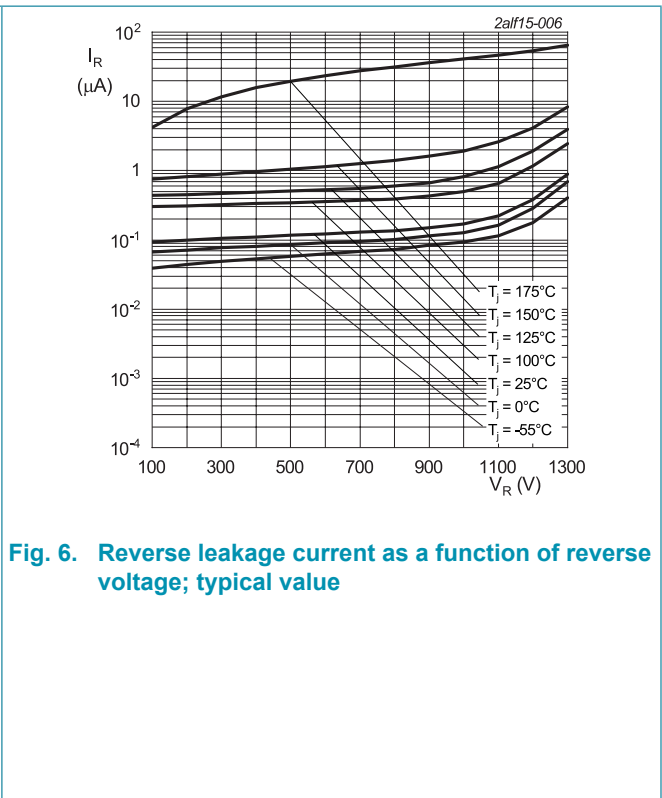
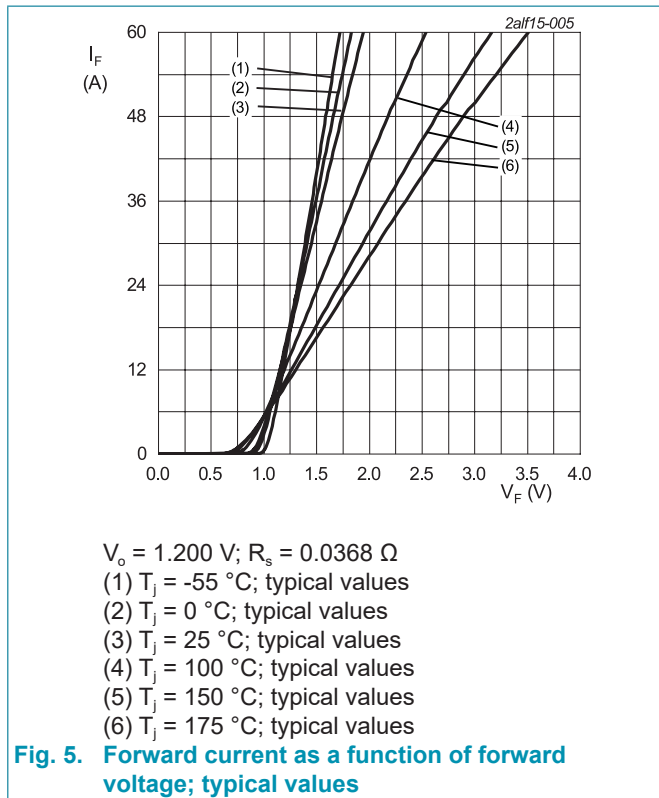


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_F$	forward current	$I_F = 30\text{ A}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 5}$		-	1.42	1.60	V
		$I_F = 30\text{ A}; T_j = 150\text{ }^\circ\text{C}; \text{Fig. 5}$		-	1.90	2.30	V
		$I_F = 30\text{ A}; T_j = 175\text{ }^\circ\text{C}; \text{Fig. 5}$		-	2.00	2.50	V
$I_R$	reverse current	$V_R = 1200\text{ V}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 6}$		-	1	150	$\mu\text{A}$
		$V_R = 1200\text{ V}; T_j = 175\text{ }^\circ\text{C}; \text{Fig. 6}$		-	50	1500	$\mu\text{A}$
<b>Dynamic characteristics</b>							
$Q_r$	recovered charge	$I_F = 30\text{ A}; V_R = 400\text{ V}; dI_F/dt = 500\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 7}$		-	68	-	nC
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 1\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	1407	-	pF
		$f = 1\text{ MHz}; V_R = 400\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	125	-	pF
		$f = 1\text{ MHz}; V_R = 800\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	93	-	pF
$E_{as}$	non-repetitive avalanche energy	$I_R = 8\text{ A}; L = 10\text{ mH}; T_{j(\text{init})} = 25\text{ }^\circ\text{C}$		300	-	-	mJ



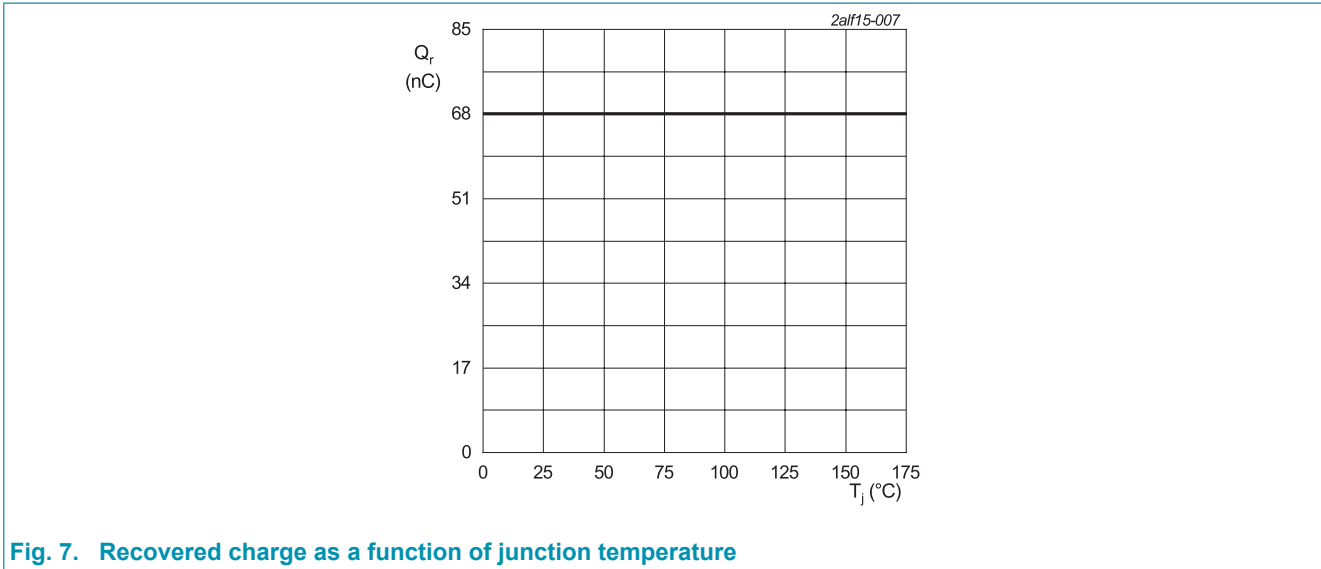
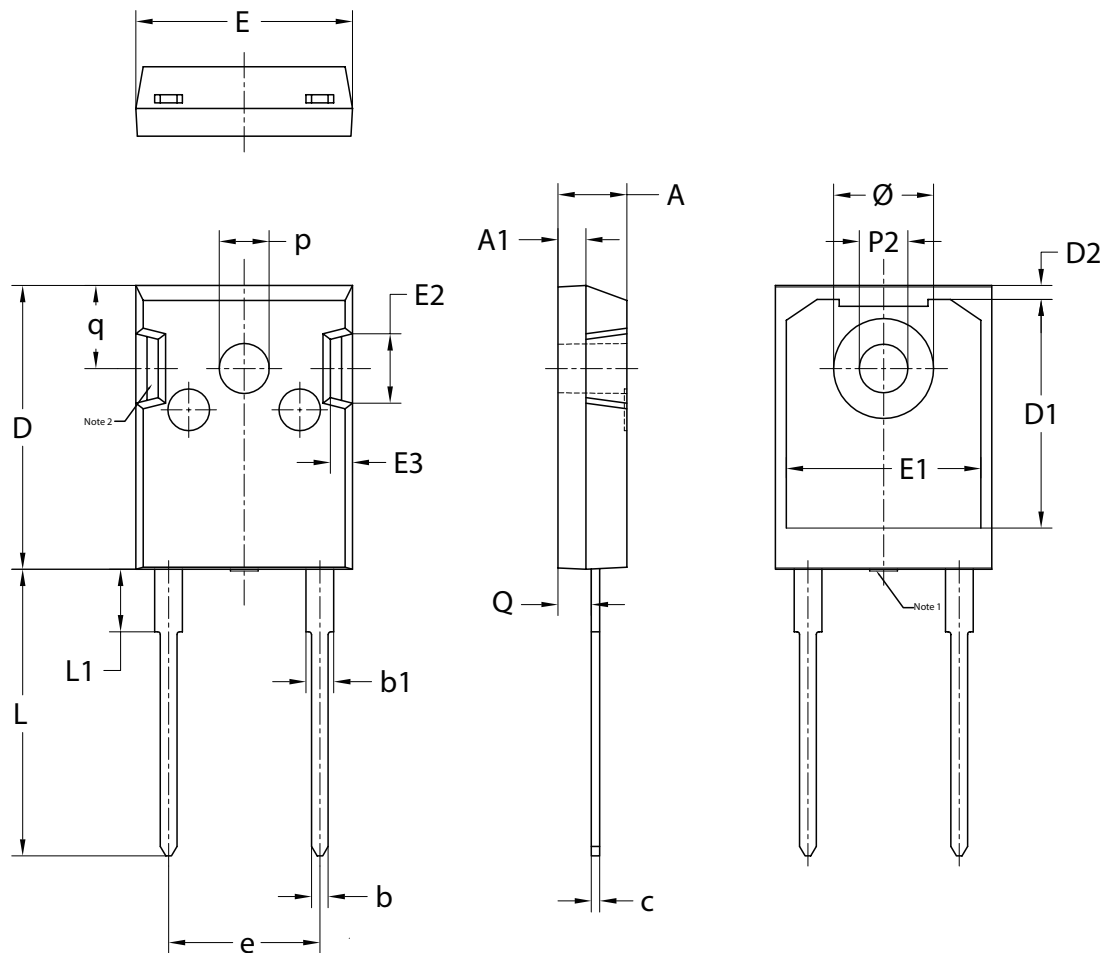


Fig. 7. Recovered charge as a function of junction temperature

### 11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 2 leads TO-247

TO247-2L



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	c	D	D <sub>1</sub>	D <sub>2</sub>	E	E <sub>1</sub>	E <sub>2</sub>	E <sub>3</sub>	e	L	L <sub>1</sub>	P <sub>2</sub>	p	Q	q	Ø
mm	5.20	2.10	1.40	2.20	0.70	20.60	16.20	1.20	15.75	14.22	5.20	1.80	10.90	20.72	4.75	3.60	3.70	2.60	6.18	7.30
	4.70	1.90	1.00	1.80	0.50	20.30	16.87	0.80	15.45	13.82	4.80	1.40	BSC	20.22	4.25	3.40	3.50	2.20	5.78	7.10

Note:

1. Mold resin protrusion max 0.127mm.
2. Metal exposed with Sn plating.



## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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